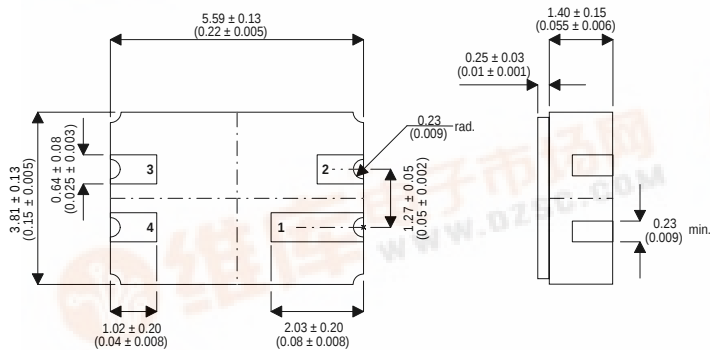


2N3439CSM4

HIGH VOLTAGE, MEDIUM POWER, NPN TRANSISTOR IN A HERMETICALLY SEALED CERAMIC SURFACE MOUNT PACKAGE FOR HIGH RELIABILITY APPLICATIONS

MECHANICAL DATA

Dimensions in mm (inches)



FEATURES

- SILICON PLANAR EPITAXIAL NPN TRANSISTOR
- HERMETIC CERAMIC SURFACE MOUNT PACKAGE
- CECC SCREENING OPTIONS
- SPACE QUALITY LEVELS OPTIONS
- HIGH VOLTAGE

LCC3 PACKAGE Underside View

PAD 1 – Collector PAD 3 – Emitter
PAD 2 – N/C PAD 4 – Base

APPLICATIONS:

Hermetically sealed surface mount version of the popular 2N3439 for high reliability / space applications requiring small size and low weight devices.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage	450V
V_{CEO}	Collector – Emitter Voltage ($I_B = 0$)	350V
V_{EBO}	Emitter – Base Voltage ($I_B = 0$)	7V
I_C	Collector Current	500mA
P_D	Total Device Dissipation	350mW
P_D	Derate above 50°C	$2.0\text{mW} / ^{\circ}\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	350°C/W
	Storage Temperature	-55 to 200°C

ELECTRICAL CHARACTERISTICS ($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{\text{CEO(sus)}}^*$ Collector – Emitter Sustaining Voltage	$I_{\text{C}} = 50\text{mA}$	350			V
I_{CEX}^* Collector Cut-off Current ($I_{\text{C}} = 0$)	$I_{\text{B}} = 0$ $V_{\text{CE}} = 450\text{V}$			500	μA
I_{CBO}^* Collector – Base Cut-off Current	$I_{\text{E}} = 0$ $V_{\text{CB}} = 300\text{V}$			20	μA
	$T_{\text{C}} = 125^{\circ}\text{C}$			10	μA
I_{EBO}^* Emitter Cut-off Current ($I_{\text{C}} = 0$)	$I_{\text{C}} = 0$ $V_{\text{EB}} = 6\text{V (off)}$			20	μA
$V_{\text{CE(sat)}}^*$ Collector – Emitter Saturation Voltage	$I_{\text{C}} = 50\text{mA}$ $I_{\text{B}} = 4\text{mA}$			0.5	V
$V_{\text{BE(sat)}}^*$ Base – Emitter Saturation Voltage	$I_{\text{C}} = 50\text{mA}$ $I_{\text{B}} = 4\text{mA}$			1.3	
h_{FE}^* DC Current Gain	$I_{\text{C}} = 20\text{mA}$ $I_{\text{C}} = 10\text{mA}$	40		160	—

* Pulse test $t_{\text{p}} = 300\mu\text{s}$, $\delta \leq 2\%$

DYNAMIC CHARACTERISTICS ($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
f_{T} Transition Frequency	$I_{\text{C}} = 10\text{mA}$ $V_{\text{CE}} = 10\text{V}$ $f = 5\text{MHz}$	15			MHz
C_{ob} Output Capacitance	$V_{\text{CB}} = 10\text{V}$ $I_{\text{E}} = 0$ $f = 1.0\text{MHz}$			10	pF
h_{fe} Small Signal Current Gain	$I_{\text{C}} = 5\text{mA}$ $V_{\text{CE}} = 10\text{V}$ $f = 1\text{kHz}$	25			